WHAT IS CLAIMED IS:

- 1. A semiconductor apparatus comprising:
 - a substrate;

m electrically conductive layers formed on said substrate, m being an integer of 2 or more, potentials of said m electrically conductive layers being capable of being independently controlled; and

semiconductor thin films including at least one semiconductor device respectively, said semiconductor thin films being bonded on surfaces of said m electrically conductive layers respectively.

- 2. The semiconductor apparatus according to claim 1, further comprising an integrated circuit formed in said substrate, said substrate being a semiconductor substrate.
- 3. The semiconductor apparatus according to claim 1, further comprising an integrated circuit device disposed on said substrate, said substrate being an insulating substrate.
- 4. The semiconductor apparatus according to claim 1, wherein said semiconductor device includes a first-conductive-type semiconductor layer and a second-conductive-type semiconductor layer,

a conductive-type of said second-conductive-type semiconductor layer being different from a conductive-type of said first-conductive-type semiconductor layer, and

said first-conductive-type semiconductor layer being in contact with said electrically conductive layer.

5. The semiconductor apparatus according to claim 1, wherein number of said semiconductor thin films is m, and said m semiconductor thin films are bonded on said m

electrically conductive layers respectively in a one-to-one correspondence.

- 6. The semiconductor apparatus according to claim 5, wherein ends of said electrically conductive layers in a row direction of said semiconductor devices and ends of said semiconductor thin films in a row direction of said semiconductor devices are located on imaginary reference planes perpendicular to a surface of said substrate in such a way that said ends of said electrically conductive layers and said ends of said semiconductor thin films are in alignment.
- 7. The semiconductor apparatus according to claim 5, wherein number of said semiconductor devices is n for each of said semiconductor thin films, n being an integer of 2 or more.
- 8. The semiconductor apparatus according to claim 1, wherein number of said semiconductor thin films bonded on said m electrically conductive layers is n for each of said electrically conductive layers, n being an integer of 2 or more.
- 9. The semiconductor apparatus according to claim 8, wherein number of said semiconductor device formed in each of said n semiconductor thin films is 1.
- 10. The semiconductor apparatus according to claim 7, further comprising:

m common wiring lines disposed on said substrate, potentials of said m common wiring lines being capable of being independently controlled, said m common wiring lines being electrically connected to said m electrically conductive layers in a one-to-one correspondence; and

n signal wiring lines disposed on said substrate, potentials of said n signal wiring lines being capable of being independently controlled;

wherein said n second-conductive-type semiconductor layers disposed on each of said m electrically conductive layers are electrically connected to said n signal wiring lines so that k-th one of said n second-conductive-type semiconductor layers and k-th one of said n signal wiring lines are electrically connected in a one-to-one correspondence, k being an integer between 1 and n.

- 11. The semiconductor apparatus according to claim 10, further comprising individual interconnecting lines extending from upper surfaces of said second-conductive-type semiconductor layers of said semiconductor devices in said semiconductor thin films to said signal wiring lines.
- 12. The semiconductor apparatus according to claim 11, wherein said individual interconnecting lines are thin films formed by photolithography.
- 13. The semiconductor apparatus according to claim 10, wherein said integrated circuit includes a driving-IC for driving said semiconductor devices, and said m common wiring lines and said n signal wiring lines are electrically connected to said driving-IC.
- 14. The semiconductor apparatus according to claim 1, wherein said semiconductor thin films mainly consist of compound semiconductor.
- 15. The semiconductor apparatus according to claim 1, wherein said semiconductor device is any of a light-emitting element, a light-sensing element, a Hall element, and a

piezoelectric element.

- 16. The semiconductor apparatus according to claim 1, wherein said electrically conductive layers are made of any of metal and polysilicon.
- 17. An optical print head including the semiconductor apparatus of claim 1.
- 18. The optical print head of claim 17, wherein the semiconductor device in the first thin semiconductor film in the semiconductor apparatus is a light-emitting element, the semiconductor apparatus including a plurality of such light-emitting elements, the optical print head further including:
- a base for supporting the combined semiconductor apparatus;
- a rod lens array for focusing the light emitted by the light-emitting elements in the combined semiconductor apparatus;
 - a holder for holding the rod lens array; and
- at least one clamp for holding the base and the holder together.
- 19. An image-forming apparatus comprising at least one optical print head including the semiconductor apparatus of claim 1.
- 20. The image-forming apparatus of claim 19, further comprising:
- a photosensitive drum selectively illuminated by the optical printing head to form a latent electrostatic image.
- 21. The image-forming apparatus of claim 20, further comprising:
- a developing unit for supplying toner to develop the latent electrostatic image on the photosensitive drum; and

a transfer roller for transferring the developed image from the photosensitive drum to printing media.